

Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
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($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	- -	MAX. 20	mA j

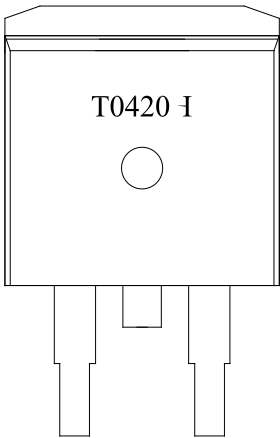
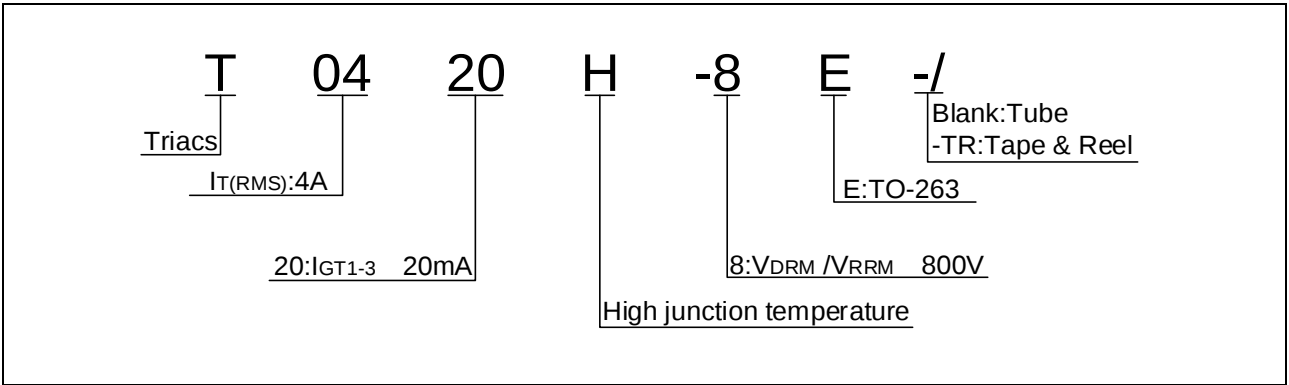


FIG.1 Maximum power dissipation versus RMS on-state current

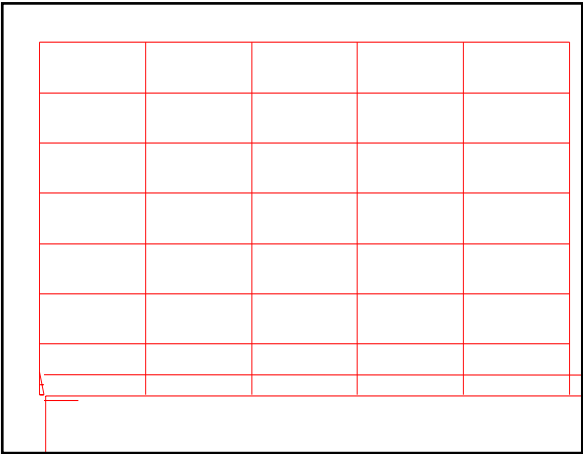
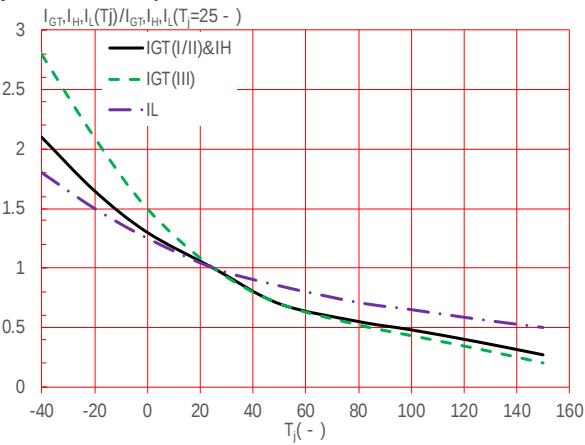
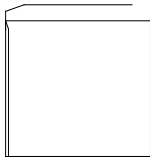


FIG.2: RMS on-state current versus case temperature (I_{RMS})

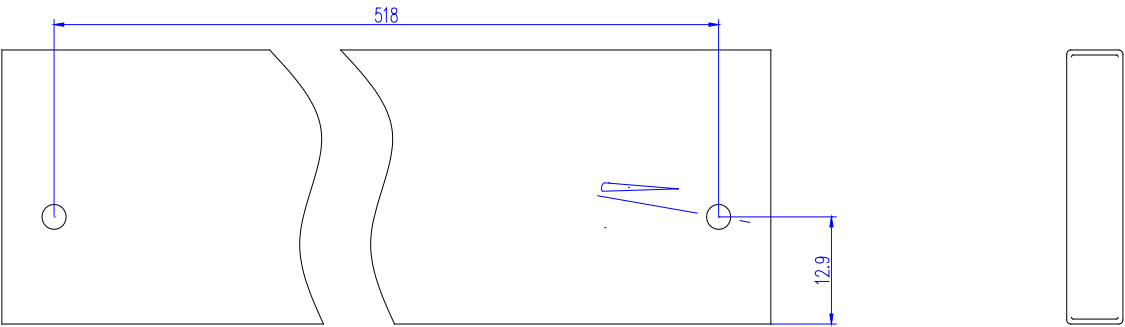
FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	
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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.37		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033
G			1.50			
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0		0.25			
M	1.25		1.35			



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